

650V GaN FET

^{1.} **Description**

The KX1N65R200PD3, 650V, 200m Ω Gallium Nitride (GaN) FETs are hybrid normally-off Gallium Nitride (GaN) field effect transistors with the strongest gate and the lowest reverse voltage drop of all wide-band-gap devices in the market. They allow simple gate drive, offer best-in-class performance and outstanding reliability.

Features

- Strong gate with a high threshold, no need for negative gate drive, and a high repetitive input voltage tolerance of ±20V.
- Fast turn-on/off speed for reduced cross-over losses.
- Low Q_G and simple gate drive for lowest driver consumption at high frequencies.
- Lowest V_F in off-state reverse conduction among all GaN FETs for low loss during dead-times.
- Low Q_{RR} for outstanding hard-switched bridge applications.
- High spike tolerance of 800V for enhanced reliability.

Benefits

- Enable very high conversion efficiencies.
- Enable higher frequency for compact power supplies.
- End-product cost & size savings due to reduced cooling requirements
- Improved safety & reliability due to cooler operation temperature

Applications

- High-frequency compact chargers with QR or ACF flyback topologies.
- Half-bridge buck/boost, totem-pole PFC circuits or inverter circuits
- High-efficiency/High-frequency LLC or other soft-switching topologies.

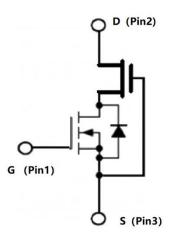
Key Performance Parameters				
V _{DSS} (V)	650			
V _{DSS(PK)} (V) ¹⁾	800			
R _{DS(ON)} (mΩ) typ ²⁾	200			
Vth(V)	1.8			
Qoss(nC) typ	37			
Q _G (nC) typ	12.6			
Q _{RR} (nC) typ	37.5			

1) Duty < 1%, spike duration < 1µs, nonrepetitive

2) Dynamic on-resistance, see below figures







Package Information		
Part #	KX1N65R200PD3	
Package	DFN8x8-3	
Size	8.0mm*8.0mm *1.0mm(H)	

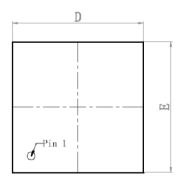
Briefing

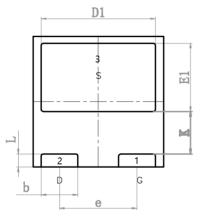
KX1N65R200PD3



^{2.} Package Dimensions

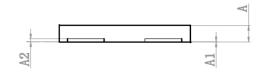
Dimension Symbol	MIN	NOM	MAX	Dimension Symbol	MIN	NOM	МАХ
Α	0.90	1.00	1.10	К		2.50	
A1	0.00		0.05	b	2.15	2.25	2.35
A2		0.20		L	0.70	0.80	0.90
D	7.90	8.00	8.10	е		4.75	
D1	6.90	7.00	7.10				
E	7.90	8.00	8.10	DFN 8x8-3 (KuanXin: KX1N65R***PD3)			
E1	4.10	4.20	4.30	Unit:	mm	Date:	Jul.,2022





Top View

Bottom View



Side View

^{3.} Revision History

Revision No.	Date	Description of Change(s)
Rev0.1	2022-07-18	Draft